

Enxia Zhang

List of Publications by Year in descending order

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192
times ranked

2473
citing authors

#	ARTICLE	IF	CITATIONS
1	Proton-Induced Dehydrogenation of Defects in AlGaIn/GaN HEMTs. IEEE Transactions on Nuclear Science, 2013, 60, 4080-4086.	1.2	136
2	Effects of Applied Bias and High Field Stress on the Radiation Response of GaN/AlGaIn HEMTs. IEEE Transactions on Nuclear Science, 2015, 62, 2423-2430.	1.2	84
3	Fin-Width Dependence of Ionizing Radiation-Induced Subthreshold-Swing Degradation in 100-nm-Gate-Length FinFETs. IEEE Transactions on Nuclear Science, 2009, 56, 3250-3255.	1.2	76
4	Influence of LDD Spacers and H ⁺ Transport on the Total-Ionizing-Dose Response of 65-nm MOSFETs Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2018, 65, 164-174.	1.2	73
5	Radiation-Induced Defect Evolution and Electrical Degradation of AlGaIn/GaN High-Electron-Mobility Transistors. IEEE Transactions on Nuclear Science, 2011, 58, 2918-2924.	1.2	69
6	Temperature Dependence and Postirradiation Annealing Response of the 1/f Noise of 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2013, 60, 2361-2367.	1.6	69
7	Impact of proton irradiation on deep level states in n-GaN. Applied Physics Letters, 2013, 103, .	1.5	59
8	Laser- and Heavy Ion-Induced Charge Collection in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2011, 58, 2563-2569.	1.2	58
9	1/f Noise in GaN HEMTs grown under Ga-rich, N-rich, and NH ₃ -rich conditions. Microelectronics Reliability, 2011, 51, 212-216.	0.9	58
10	The Impact of X-Ray and Proton Irradiation on HfO ₂ -Based Bipolar Resistive Memories. IEEE Transactions on Nuclear Science, 2013, 60, 4540-4546.	1.2	58
11	Bias Dependence of Total Ionizing Dose Effects in SiGe-MOS FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2834-2838.	1.2	57
12	Low-Energy X-ray and Ozone-Exposure Induced Defect Formation in Graphene Materials and Devices. IEEE Transactions on Nuclear Science, 2011, 58, 2961-2967.	1.2	56
13	Total-Ionizing-Dose Radiation Effects in AlGaIn/GaN HEMTs and MOS-HEMTs. IEEE Transactions on Nuclear Science, 2013, 60, 4074-4079.	1.2	55
14	Analysis of TID Process, Geometry, and Bias Condition Dependence in 14-nm FinFETs and Implications for RF and SRAM Performance. IEEE Transactions on Nuclear Science, 2017, 64, 285-292.	1.2	55
15	Geometry Dependence of Total-Dose Effects in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2951-2958.	1.2	54
16	Effects of Proton-Induced Displacement Damage on Gallium Nitride HEMTs in RF Power Amplifier Applications. IEEE Transactions on Nuclear Science, 2015, 62, 2417-2422.	1.2	53
17	Charge Trapping in Al ₂ O ₃ /Ga ₂ O ₃ -Based MOS Capacitors. IEEE Electron Device Letters, 2018, 39, 1022-1025.	2.2	50
18	Process Dependence of Proton-Induced Degradation in GaN HEMTs. IEEE Transactions on Nuclear Science, 2010, .	1.2	49

#	ARTICLE	IF	CITATIONS
19	A brief overview of gate oxide defect properties and their relation to MOSFET instabilities and device and circuit time-dependent variability. <i>Microelectronics Reliability</i> , 2018, 81, 186-194.	0.9	49
20	Multiple Defects Cause Degradation After High Field Stress in AlGaIn/GaN HEMTs. <i>IEEE Transactions on Device and Materials Reliability</i> , 2018, 18, 364-376.	1.5	49
21	Comparison of Charge Pumping and $\frac{1}{f}$ Noise in Irradiated Ge pMOSFETs. <i>IEEE Transactions on Nuclear Science</i> , 2012, 59, 735-741.	1.2	47
22	Worst-Case Bias for Proton and 10-keV X-Ray Irradiation of AlGaIn/GaN HEMTs. <i>IEEE Transactions on Nuclear Science</i> , 2017, 64, 218-225.	1.2	46
23	Temperature-dependence and microscopic origin of low frequency $1/f$ noise in GaN/AlGaIn high electron mobility transistors. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	44
24	Device and circuit-level analog performance trade-offs: a comparative study of planar bulk FETs versus FinFETs. , 0, , .		43
25	Heavy-Ion-Induced Current Transients in Bulk and SOI FinFETs. <i>IEEE Transactions on Nuclear Science</i> , 2012, 59, 2674-2681.	1.2	43
26	Total-Ionizing-Dose Effects on Threshold Switching in $1T1R$ Charge Density Wave Devices. <i>IEEE Electron Device Letters</i> , 2017, 38, 1724-1727.	2.2	39
27	Defects and Low-Frequency Noise in Irradiated Black Phosphorus MOSFETs With HfO_2 Gate Dielectrics. <i>IEEE Transactions on Nuclear Science</i> , 2018, 65, 1227-1238.	1.2	39
28	Ozone-exposure and annealing effects on graphene-on-SiO ₂ transistors. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	38
29	Effects of Bias on the Irradiation and Annealing Responses of 4H-SiC MOS Devices. <i>IEEE Transactions on Nuclear Science</i> , 2011, 58, 2925-2929.	1.2	37
30	Origins of Low-Frequency Noise and Interface Traps in 4H-SiC MOSFETs. <i>IEEE Electron Device Letters</i> , 2013, 34, 117-119.	2.2	37
31	Single- and Multiple-Event Induced Upsets in $1T1R$ RRAM. <i>IEEE Transactions on Nuclear Science</i> , 2014, 61, 1717-1725.	1.2	37
32	Bias Dependence of Total-Dose Effects in Bulk FinFETs. <i>IEEE Transactions on Nuclear Science</i> , 2013, 60, 4476-4482.	1.2	35
33	Correlation of proton irradiation induced threshold voltage shifts to deep level traps in AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	35
34	Fin Width and Bias Dependence of the Response of Triple-Gate MOSFETs to Total Dose Irradiation. <i>IEEE Transactions on Nuclear Science</i> , 2011, 58, 2871-2875.	1.2	34
35	Total Ionizing Dose Radiation Effects on 14 nm FinFET and SOI UTBB Technologies. , 2015, , .		33
36	Radiation Effects in AlGaIn/GaN HEMTs. <i>IEEE Transactions on Nuclear Science</i> , 2022, 69, 1105-1119.	1.2	32

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37	Atomic-scale origins of bias-temperature instabilities in SiCâ€“SiO ₂ structures. Applied Physics Letters, 2011, 98, .	1.5	31
38	1/ f Noise in As-Processed and Proton-Irradiated AlGa _N /Ga _N HEMTs Due to Carrier Number Fluctuations. IEEE Transactions on Nuclear Science, 2017, 64, 181-189.	1.2	31
39	Proton-irradiation-immune electronics implemented with two-dimensional charge-density-wave devices. Nanoscale, 2019, 11, 8380-8386.	2.8	29
40	Total-Ionizing-Dose Effects and Low-Frequency Noise in 30-nm Gate-Length Bulk and SOI FinFETs With SiO ₂ /HfO ₂ Gate Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 245-252.	1.2	29
41	Total Ionizing Dose (TID) Effects in Extremely Scaled Ultra-Thin Channel Nanowire (NW) Gate-All-Around (GAA) InGaAs MOSFETs. IEEE Transactions on Nuclear Science, 2015, 62, 2888-2893.	1.2	28
42	Total Ionizing Dose Effects on Strained Ge pMOS FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2017, 64, 226-232.	1.2	28
43	TID and Displacement Damage Resilience of 1T1R $\frac{HfO_2}{Hf}$ Resistive Memories. IEEE Transactions on Nuclear Science, 2014, 61, 2972-2978.	1.2	27
44	Total Ionizing Dose Effects on hBN Encapsulated Graphene Devices. IEEE Transactions on Nuclear Science, 2014, 61, 2868-2873.	1.2	27
45	Total-Ionizing-Dose Effects and Low-Frequency Noise in 16-nm InGaAs FinFETs With HfO ₂ /Al ₂ O ₃ Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 210-220.	1.2	26
46	Time-Domain Reflectometry Measurements of Total-Ionizing-Dose Degradation of nMOSFETs. IEEE Transactions on Nuclear Science, 2013, 60, 4470-4475.	1.2	25
47	Charge Collection Mechanisms in AlGa _N /Ga _N MOS High Electron Mobility Transistors. IEEE Transactions on Nuclear Science, 2013, 60, 4439-4445.	1.2	25
48	High-Field Stress, Low-Frequency Noise, and Long-Term Reliability of AlGa _N /Ga _N HEMTs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 282-289.	1.5	25
49	SEB Hardened Power MOSFETs With High-K Dielectrics. IEEE Transactions on Nuclear Science, 2015, 62, 2830-2836.	1.2	24
50	Angular Effects on Single-Event Mechanisms in Bulk FinFET Technologies. IEEE Transactions on Nuclear Science, 2018, 65, 223-230.	1.2	24
51	Dose-Rate Dependence of the Total-Ionizing-Dose Response of Ga _N -Based HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 170-176.	1.2	24
52	Thermal stability of deep level defects induced by high energy proton irradiation in n-type Ga _N . Journal of Applied Physics, 2015, 118, .	1.1	23
53	Temperature-Dependent Efficiency Droop in Ga _N -Based Blue LEDs. IEEE Electron Device Letters, 2018, 39, 528-531.	2.2	23
54	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2014, 61, 3210-3217.	1.2	22

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55	Advanced SiGe BiCMOS Technology for Multi-Mrad Electronic Systems. IEEE Transactions on Device and Materials Reliability, 2014, 14, 844-848.	1.5	22
56	Effect of Device Variants in 32Ånm and 45Ånm SOI on SET Pulse Distributions. IEEE Transactions on Nuclear Science, 2013, 60, 4399-4404.	1.2	21
57	RF Performance of Proton-Irradiated AlGaIn/GaN HEMTs. IEEE Transactions on Nuclear Science, 2014, 61, 2959-2964.	1.2	21
58	Charge Transport in Vertical GaN Schottky Barrier Diodes: A Refined Physical Model for Conductive Dislocations. IEEE Transactions on Electron Devices, 2020, 67, 841-846.	1.6	21
59	Sensitivity of High-Frequency RF Circuits to Total Ionizing Dose Degradation. IEEE Transactions on Nuclear Science, 2013, 60, 4498-4504.	1.2	20
60	Single-Event Transient Response of InGaAs MOSFETs. IEEE Transactions on Nuclear Science, 2014, 61, 3550-3556.	1.2	20
61	Electrical Stress and Total Ionizing Dose Effects on MoS_2 Transistors. IEEE Transactions on Nuclear Science, 2014, 61, 2862-2867.	1.2	20
62	Effects of Total-Ionizing-Dose Irradiation on SEU- and SET-Induced Soft Errors in Bulk 40-nm Sequential Circuits. IEEE Transactions on Nuclear Science, 2017, 64, 471-476.	1.2	20
63	The Impact of Charge Collection Volume and Parasitic Capacitance on SEUs in SOI- and Bulk-FinFET D Flip-Flops. IEEE Transactions on Nuclear Science, 2018, 65, 326-330.	1.2	20
64	Including the Effects of Process-Related Variability on Radiation Response in Advanced Foundry Process Design Kits. IEEE Transactions on Nuclear Science, 2010, , .	1.2	19
65	Total Ionizing Dose Effects on HfO_2 -Passivated Black Phosphorus Transistors. IEEE Transactions on Nuclear Science, 2017, 64, 170-175.	1.2	19
66	Enhanced Charge Collection in SiC Power MOSFETs Demonstrated by Pulse-Laser Two-Photon Absorption SEE Experiments. IEEE Transactions on Nuclear Science, 2019, 66, 1694-1701.	1.2	19
67	Impact of Back-Gate Bias and Device Geometry on the Total Ionizing Dose Response of 1-Transistor Floating Body RAMs. IEEE Transactions on Nuclear Science, 2012, 59, 2966-2973.	1.2	18
68	Two-Photon Absorption Induced Single-Event Effects: Correlation Between Experiment and Simulation. IEEE Transactions on Nuclear Science, 2015, 62, 2867-2873.	1.2	18
69	Scaling Effects on Single-Event Transients in InGaAs FinFETs. IEEE Transactions on Nuclear Science, 2018, 65, 296-303.	1.2	18
70	Trade-Offs Between RF Performance and Total-Dose Tolerance in 45-nm RF-CMOS. IEEE Transactions on Nuclear Science, 2011, 58, 2830-2837.	1.2	17
71	Understanding Charge Collection Mechanisms in InGaAs FinFETs Using High-Speed Pulsed-Laser Transient Testing With Tunable Wavelength. IEEE Transactions on Nuclear Science, 2017, 64, 2069-2078.	1.2	17
72	Gate Bias and Geometry Dependence of Total-Ionizing-Dose Effects in InGaAs Quantum-Well MOSFETs. IEEE Transactions on Nuclear Science, 2017, 64, 239-244.	1.2	17

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73	Gate Bias and Length Dependences of Total Ionizing Dose Effects in InGaAs FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2019, 66, 1599-1605.	1.2	17
74	Comparison of Total-Ionizing-Dose Effects in Bulk and SOI FinFETs at 90 and 295 K. IEEE Transactions on Nuclear Science, 2019, 66, 911-917.	1.2	17
75	Total-Ionizing-Dose Response of Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 687-696.	1.2	17
76	Electrical Stress and Total Ionizing Dose Effects on Graphene-Based Non-Volatile Memory Devices. IEEE Transactions on Nuclear Science, 2012, 59, 2974-2978.	1.2	16
77	Effects of Negative-Bias-Temperature-Instability on Low-Frequency Noise in SiGe p MOSFETs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 541-548.	1.5	16
78	Low Energy Proton Irradiation Effects on Commercial Enhancement Mode GaN HEMTs. IEEE Transactions on Nuclear Science, 2017, 64, 253-257.	1.2	16
79	Effect of Transistor Variants on Single-Event Transients at the 14-/16-nm Bulk FinFET Technology Generation. IEEE Transactions on Nuclear Science, 2018, 65, 1807-1813.	1.2	16
80	Effects of Halo Doping and Si Capping Layer Thickness on Total-Dose Effects in Ge p-MOSFETs. IEEE Transactions on Nuclear Science, 2010, 57, 1933-1939.	1.2	15
81	Layout-Related Stress Effects on Radiation-Induced Leakage Current. IEEE Transactions on Nuclear Science, 2010, , .	1.2	15
82	Single-Event Transient Sensitivity of InAlSb/InAs/AlGaSb High Electron Mobility Transistors. IEEE Transactions on Nuclear Science, 2012, 59, 2691-2696.	1.2	15
83	Radiation Effects on LiNbO ₂ Memristors for Neuromorphic Computing Applications. IEEE Transactions on Nuclear Science, 2013, 60, 4555-4562.	1.2	15
84	Heavy-Ion and Laser Induced Charge Collection in SiGe Channel p MOSFETs. IEEE Transactions on Nuclear Science, 2014, 61, 3187-3192.	1.2	15
85	Impact of Technology Scaling in sub-100Ånm nMOSFETs on Total-Dose Radiation Response and Hot-Carrier Reliability. IEEE Transactions on Nuclear Science, 2014, 61, 1426-1432.	1.2	15
86	Radiation-Induced Charge Trapping and Low-Frequency Noise of Graphene Transistors. IEEE Transactions on Nuclear Science, 2018, 65, 156-163.	1.2	15
87	Length and fin number dependence of ionizing radiation-induced degradation in bulk FinFETs. , 2013, , .		14
88	Single-Event Transient Induced Harmonic Errors in Digitally Controlled Ring Oscillators. IEEE Transactions on Nuclear Science, 2014, 61, 3163-3170.	1.2	14
89	Strong Correlation Between Experiment and Simulation for Two-Photon Absorption Induced Carrier Generation. IEEE Transactions on Nuclear Science, 2017, 64, 1133-1136.	1.2	14
90	Impact of Single-Event Transient Duration and Electrical Delay at Reduced Supply Voltages on SET Mitigation Techniques. IEEE Transactions on Nuclear Science, 2018, 65, 362-368.	1.2	14

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91	Dynamic Modeling of Radiation-Induced State Changes in HfO_2/Hf 1T1R RRAM. IEEE Transactions on Nuclear Science, 2014, 61, 3497-3503.	1.2	13
92	Exploiting Parallelism and Heterogeneity in a Radiation Effects Test Vehicle for Efficient Single-Event Characterization of Nanoscale Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 486-494.	1.2	13
93	Dual-Interlocked Logic for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2018, 65, 1872-1878.	1.2	13
94	Low-frequency noise and defects in copper and ruthenium resistors. Applied Physics Letters, 2019, 114, .	1.5	13
95	Total-Ionizing-Dose Effects on InGaAs FinFETs With Modified Gate-stack. IEEE Transactions on Nuclear Science, 2020, 67, 253-259.	1.2	13
96	Total Ionizing Dose Responses of 22-nm FDSOI and 14-nm Bulk FinFET Charge-Trap Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 677-686.	1.2	13
97	Effect of Ionizing Radiation on Defects and $1/f$ Noise in Ge pMOSFETs. IEEE Transactions on Nuclear Science, 2011, 58, 764-769.	1.2	12
98	Pulsed laser-induced transient currents in bulk and silicon-on-insulator FinFETs. , 2011, , .		12
99	Charge Pumping Measurements of Radiation-Induced Interface-Trap Density in Floating-Body SOI FinFETs. IEEE Transactions on Nuclear Science, 2012, 59, 3062-3068.	1.2	12
100	Surface Reactions and Defect Formation in Irradiated Graphene Devices. IEEE Transactions on Nuclear Science, 2012, 59, 3039-3044.	1.2	12
101	Total Ionizing Dose Radiation Effects in Al_2O_3 -Gated Ultra-Thin Body $\text{In}_{0.7}\text{Ga}_{0.3}\text{As}$ MOSFETs. IEEE Transactions on Nuclear Science, 2013, 60, 402-407.	1.2	12
102	Capacitance-Frequency Estimates of Border-Trap Densities in Multifin MOS Capacitors. IEEE Transactions on Nuclear Science, 2018, 65, 175-183.	1.2	12
103	Total-Ionizing-Dose Responses of GaN-Based HEMTs With Different Channel Thicknesses and MOSHEMTs With Epitaxial MgCaO as Gate Dielectric. IEEE Transactions on Nuclear Science, 2018, 65, 46-52.	1.2	12
104	Total-Ionizing-Dose Effects on 3D Sequentially Integrated, Fully Depleted Silicon-on-Insulator MOSFETs. IEEE Electron Device Letters, 2020, 41, 637-640.	2.2	12
105	Worst-Case Bias for High Voltage, Elevated-Temperature Stress of AlGaIn/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2020, 20, 420-428.	1.5	12
106	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2019, 66, 125-133.	1.2	11
107	3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2021, 68, 2556-2563.	1.6	11
108	TID Effects in Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2022, 69, 1444-1452.	1.2	11

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109	Accelerated Oxidation of Silicon Due to X-ray Irradiation. IEEE Transactions on Nuclear Science, 2012, 59, 781-785.	1.2	10
110	Impact of Total Ionizing Dose on a 4th Generation, 90Ånm SiGe HBT Gaussian Pulse Generator. IEEE Transactions on Nuclear Science, 2014, 61, 3050-3054.	1.2	10
111	Total Dose Effects in Tunnel-Diode Body-Contact SOI & MOSFETs. IEEE Transactions on Nuclear Science, 2014, 61, 3018-3022.	1.2	10
112	Charge Collection Mechanisms in GaAs MOSFETs. IEEE Transactions on Nuclear Science, 2015, 62, 2752-2759.	1.2	10
113	Total-Ionizing-Dose Effects in Piezoresistive Micromachined Cantilevers. IEEE Transactions on Nuclear Science, 2017, 64, 263-268.	1.2	10
114	Impact of discrete trapping in high pressure deuterium annealed and doped poly-Si channel 3D NAND macaroni. , 2017, , .		10
115	Impact of Temporal Masking of Flip-Flop Upsets on Soft Error Rates of Sequential Circuits. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	10
116	Effects of Temperature and Supply Voltage on SEU- and SET-Induced Errors in Bulk 40-nm Sequential Circuits. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	10
117	Total Ionizing Dose (TID) Effects in Ultra-Thin Body Ge-on-Insulator (GOI) Junctionless CMOSFETs With Recessed Source/Drain and Channel. IEEE Transactions on Nuclear Science, 2017, 64, 176-180.	1.2	10
118	The Impact of Proton-Induced Single Events on Image Classification in a Neuromorphic Computing Architecture. IEEE Transactions on Nuclear Science, 2020, 67, 108-115.	1.2	10
119	Impacts of Through-Silicon Vias on Total-Ionizing-Dose Effects and Low-Frequency Noise in FinFETs. IEEE Transactions on Nuclear Science, 2021, 68, 740-747.	1.2	10
120	Effects of Processing and Radiation Bias on Leakage Currents in Ge pMOSFETs. IEEE Transactions on Nuclear Science, 2010, , .	1.2	9
121	Activation Energies for Oxide- and Interface-Trap Charge Generation Due to Negative-Bias Temperature Stress of Si-Capped SiGe-pMOSFETs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 352-358.	1.5	9
122	X-Ray and Proton Radiation Effects on 40 nm CMOS Physically Unclonable Function Devices. IEEE Transactions on Nuclear Science, 2018, 65, 1519-1524.	1.2	9
123	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	1.2	9
124	Irradiation and Temperature Effects for a 32Ånm RF Silicon-on-Insulator CMOS Process. IEEE Transactions on Nuclear Science, 2014, 61, 3037-3042.	1.2	8
125	Charge Collection Mechanisms of Ge-Channel Bulk & MOSFETs. IEEE Transactions on Nuclear Science, 2015, 62, 2725-2731.	1.2	8
126	Empirical Modeling of FinFET SEU Cross Sections Across Supply Voltage. IEEE Transactions on Nuclear Science, 2019, 66, 1427-1432.	1.2	8

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127	Pulsed-Laser Induced Single-Event Transients in InGaAs FinFETs on Bulk Silicon Substrates. IEEE Transactions on Nuclear Science, 2019, 66, 376-383.	1.2	8
128	Polarization Dependence of Pulsed Laser-Induced SEEs in SOI FinFETs. IEEE Transactions on Nuclear Science, 2020, 67, 38-43.	1.2	8
129	Total Ionizing Dose Effects on Ge Channel $\text{p}^+\text{n}^+\text{p}$ FETs with Raised $\text{Si}_{0.55}\text{m Ge}_{0.45}$ Source/Drain. IEEE Transactions on Nuclear Science, 2015, 62, 2412-2416.	1.2	7
130	Proton-Induced Displacement Damage and Total-Ionizing-Dose Effects on Silicon-Based MEMS Resonators. IEEE Transactions on Nuclear Science, 2018, 65, 34-38.	1.2	7
131	Single-Event Transient Response of Vertical and Lateral Waveguide-Integrated Germanium Photodiodes. IEEE Transactions on Nuclear Science, 2021, 68, 801-806.	1.2	7
132	Variability in Total-Ionizing-Dose Response of Fourth-Generation SiGe HBTs. IEEE Transactions on Nuclear Science, 2021, 68, 949-957.	1.2	7
133	Aging Effects and Latent Interface-Trap Buildup in MOS Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 2724-2735.	1.2	7
134	Impact of body tie and Source/Drain contact spacing on the hot carrier reliability of 45-nm RF-CMOS. , 2010, , .		6
135	Analysis of TPA Pulsed-Laser-Induced Single-Event Latchup Sensitive-Area. IEEE Transactions on Nuclear Science, 2018, 65, 502-509.	1.2	6
136	Total Ionizing Dose Effects and Proton-Induced Displacement Damage on MoS_2 -Interlayer- MoS_2 -Tunneling Junctions. IEEE Transactions on Nuclear Science, 2019, 66, 420-427.	1.2	6
137	Total-Ionizing-Dose Response of MoS_2 Transistors With ZrO_2 and h-BN Gate Dielectrics. IEEE Transactions on Nuclear Science, 2019, 66, 1584-1591.	1.2	6
138	Supply Voltage Dependence of Ring Oscillator Frequencies for Total Ionizing Dose Exposures for 7-nm Bulk FinFET Technology. IEEE Transactions on Nuclear Science, 2021, 68, 1579-1584.	1.2	6
139	Mitigating Total-Ionizing-Dose-Induced Threshold-Voltage Shifts Using Back-Gate Biasing in 22-nm FD-SOI Transistors. IEEE Transactions on Nuclear Science, 2022, 69, 374-380.	1.2	6
140	The Quad-Path Hardening Technique for Switched-Capacitor Circuits. IEEE Transactions on Nuclear Science, 2013, 60, 4356-4361.	1.2	5
141	Proton irradiation-induced traps causing V_T instabilities and RF degradation in GaN HEMTs. , 2015, , .		5
142	Persistent Laser-Induced Leakage in a 20 nm Charge-Pump Phase-Locked Loop (PLL). IEEE Transactions on Nuclear Science, 2017, 64, 512-518.	1.2	5
143	Total Ionizing Dose Effects on a High-Voltage ($\approx 30\text{V}$) Complementary SiGe on SOI Technology. IEEE Transactions on Nuclear Science, 2017, 64, 277-284.	1.2	5
144	Comparison of Sensitive Volumes Associated With Ion- and Laser-Induced Charge Collection in an Epitaxial Silicon Diode. IEEE Transactions on Nuclear Science, 2020, 67, 57-62.	1.2	5

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145	Charge Trapping and Transconductance Degradation in Irradiated 3-D Sequentially Integrated FDSOI MOSFETs. IEEE Transactions on Nuclear Science, 2021, 68, 707-715.	1.2	5
146	Comparison of Single-Event Transients in an Epitaxial Silicon Diode Resulting From Heavy-Ion-, Focused X-Ray-, and Pulsed Laser-Induced Charge Generation. IEEE Transactions on Nuclear Science, 2021, 68, 626-633.	1.2	5
147	Mitigation of Total Dose Performance Degradation in an 8â€“18ÂGHz SiGe Reconfigurable Receiver. IEEE Transactions on Nuclear Science, 2014, 61, 3226-3235.	1.2	4
148	Total ionizing dose effects in passivated and unpassivated AlGaIn/GaN HEMTs. , 2016, , .		4
149	Analysis of temporal masking effect on single-event upset rates for sequential circuits. , 2016, , .		4
150	Total Ionizing Dose (TID) Effects in GaAs MOSFETs With La-Based Epitaxial Gate Dielectrics. IEEE Transactions on Nuclear Science, 2017, 64, 164-169.	1.2	4
151	Dose-Rate Effects on the Total-Ionizing-Dose Response of Piezoresistive Micromachined Cantilevers. IEEE Transactions on Nuclear Science, 2018, 65, 58-63.	1.2	4
152	Total-Ionizing-Dose Response of Nb₂O₅-Based MIM Diodes for Neuromorphic Computing Applications. IEEE Transactions on Nuclear Science, 2018, 65, 78-83.	1.2	4
153	Total-Ionizing-Dose Effects in InGaAs MOSFETs With High- <i>k</i> Gate Dielectrics and InP Substrates. IEEE Transactions on Nuclear Science, 2020, 67, 1312-1319.	1.2	4
154	Total-Ionizing-Dose Effects on Polycrystalline-Si Channel Vertical-Charge-Trapping Nand Devices. IEEE Transactions on Nuclear Science, 2022, 69, 314-320.	1.2	4
155	Reliability-limiting defects in AlGaIn/GaN HEMTs. , 2011, , .		3
156	Heavy-Ion Induced SETs in 32nm SOI Inverter Chains. , 2015, , .		3
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